

Heterojunction Bipolar Transistor Technology (InGaP HBT)

Broadband High Linearity Amplifier

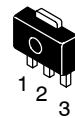
The MMG3015N is a General Purpose Amplifier that is internally Input and output matched. It is designed for a broad range of Class A, small-signal, high linearity, general purpose applications. It is suitable for applications with frequencies from 0 to 6000 MHz such as Cellular, PCS, BWA, WLL, PHS, CATV, VHF, UHF, UMTS and general small-signal RF.

Features

- Frequency: 0-6000 MHz
- P1dB: 20.5 dBm @ 900 MHz
- Small Signal Gain: 15.5 dB @ 900 MHz
- Third Order Output Intercept Point: 36 dBm @ 900 MHz
- Single 5 Volt Supply
- Active Bias
- Internally Matched to 50 Ohms
- Low Cost SOT-89 Surface Mount Package
- RoHS Compliant
- In Tape and Reel. T1 Suffix = 1,000 Units per 12 mm, 7 inch Reel.

MMG3015NT1

**0-6000 MHz, 15.5 dB
20.5 dBm
InGaP HBT**



**CASE 1514-02, STYLE 1
SOT-89
PLASTIC**

Table 1. Typical Performance (1)

Characteristic	Symbol	900 MHz	2140 MHz	3500 MHz	Unit
Small-Signal Gain (S21)	G_p	15.5	14.5	12.5	dB
Input Return Loss (S11)	IRL	-15	-19	-19	dB
Output Return Loss (S22)	ORL	-13	-9	-7	dB
Power Output @1dB Compression	P1db	20.5	20.5	18.5	dBm
Third Order Output Intercept Point	IP3	36	33.5	30.5	dBm

1. $V_{CC} = 5$ Vdc, $T_C = 25^\circ\text{C}$, 50 ohm system

Table 2. Maximum Ratings

Rating	Symbol	Value	Unit
Supply Voltage (2)	V_{CC}	7	V
Supply Current (2)	I_{CC}	300	mA
RF Input Power	P_{in}	12	dBm
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction Temperature (3)	T_J	150	$^\circ\text{C}$

2. Continuous voltage and current applied to device.

3. For reliable operation, the junction temperature should not exceed 150°C .

Table 3. Thermal Characteristics ($V_{CC} = 5$ Vdc, $I_{CC} = 95$ mA, $T_C = 25^\circ\text{C}$)

Characteristic	Symbol	Value (4)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	41.5	$^\circ\text{C}/\text{W}$

4. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 4. Electrical Characteristics ($V_{CC} = 5$ Vdc, 900 MHz, $T_C = 25^\circ\text{C}$, 50 ohm system, in Freescale Application Circuit)

Characteristic	Symbol	Min	Typ	Max	Unit
Small-Signal Gain (S21)	G_p	14	15.5	—	dB
Input Return Loss (S11)	IRL	—	-15	—	dB
Output Return Loss (S22)	ORL	—	-13	—	dB
Power Output @ 1dB Compression	P1dB	—	20.5	—	dBm
Third Order Output Intercept Point	IP3	—	36	—	dBm
Noise Figure	NF	—	5.6	—	dB
Supply Current (1)	I_{CC}	80	95	120	mA
Supply Voltage (1)	V_{CC}	—	5	—	V

1. For reliable operation, the junction temperature should not exceed 150°C .

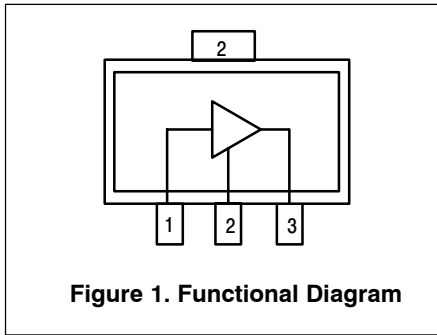


Table 5. Functional Pin Description

Pin Number	Pin Function
1	RF _{in}
2	Ground
3	RF _{out} /DC Supply

Table 6. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD 22-A114)	1C (Minimum)
Machine Model (per EIA/JESD 22-A115)	A (Minimum)
Charge Device Model (per JESD 22-C101)	IV (Minimum)

Table 7. Moisture Sensitivity Level

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113, IPC/JEDEC J-STD-020	1	260	°C

50 OHM TYPICAL CHARACTERISTICS

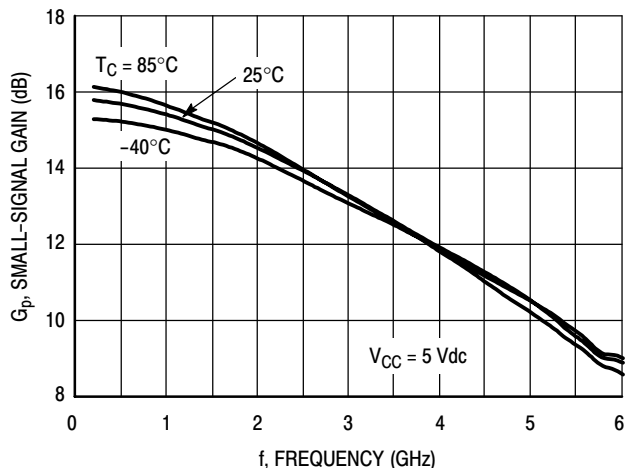


Figure 2. Small-Signal Gain (S21) versus Frequency

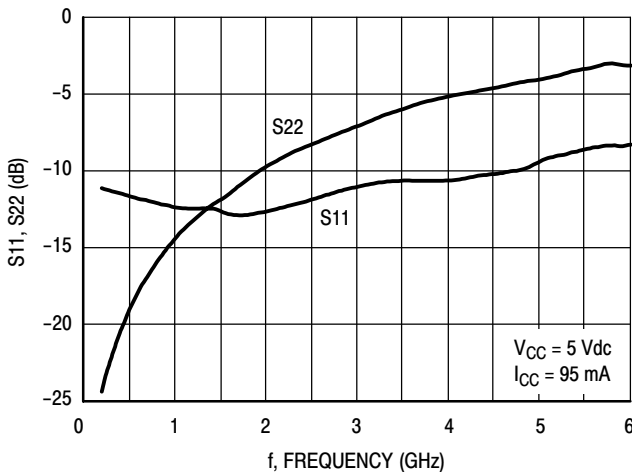


Figure 3. Input/Output Loss versus Frequency

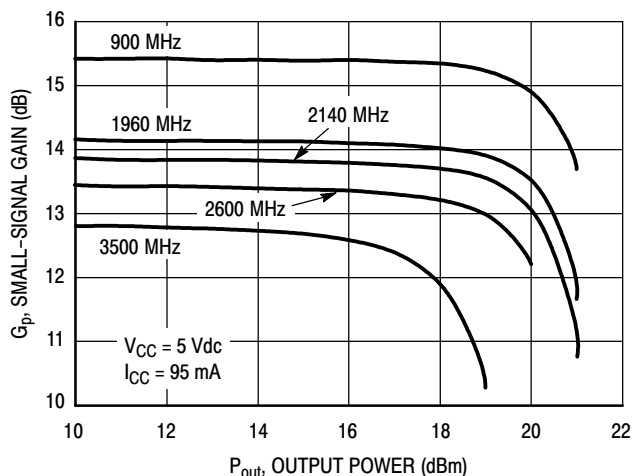


Figure 4. Small-Signal Gain versus Output Power

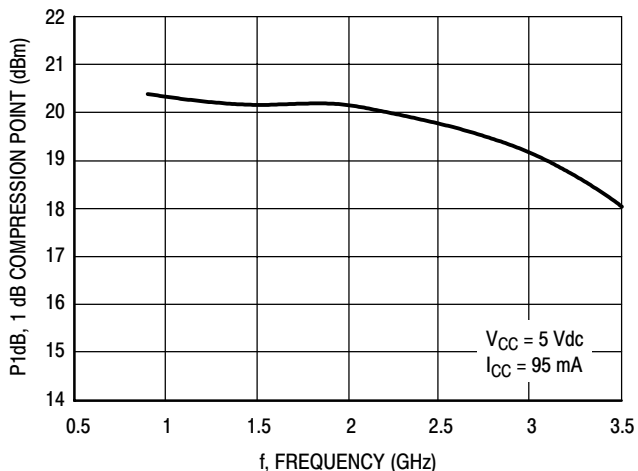


Figure 5. P1dB versus Frequency

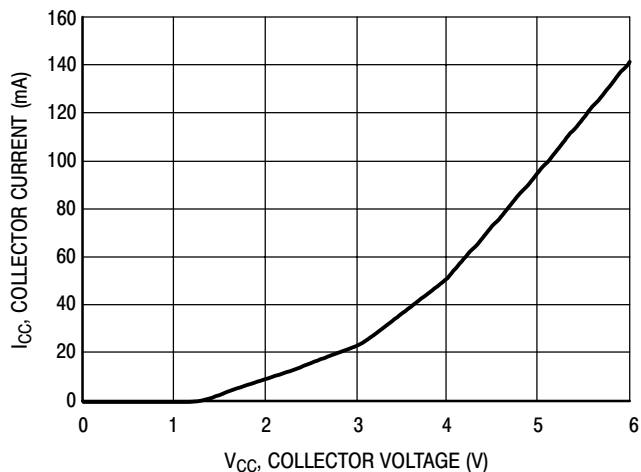


Figure 6. Collector Current versus Collector Voltage

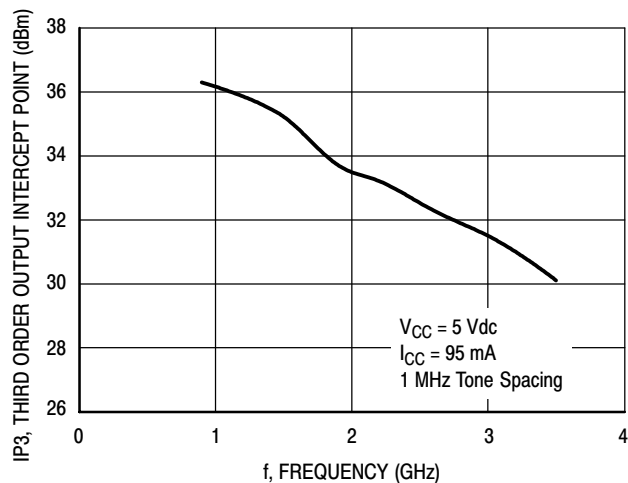


Figure 7. Third Order Output Intercept Point versus Frequency

50 OHM TYPICAL CHARACTERISTICS

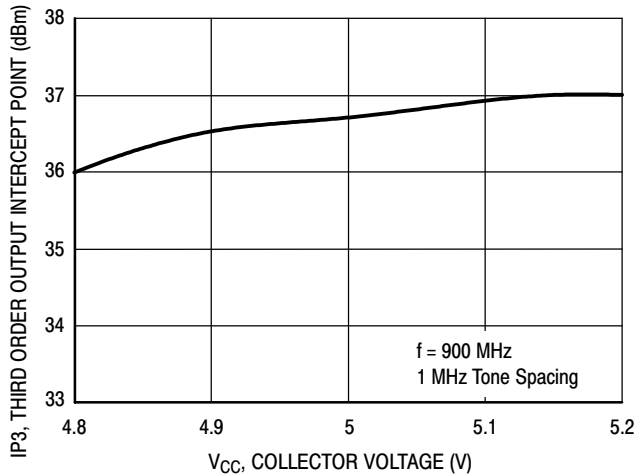


Figure 8. Third Order Output Intercept Point versus Collector Voltage

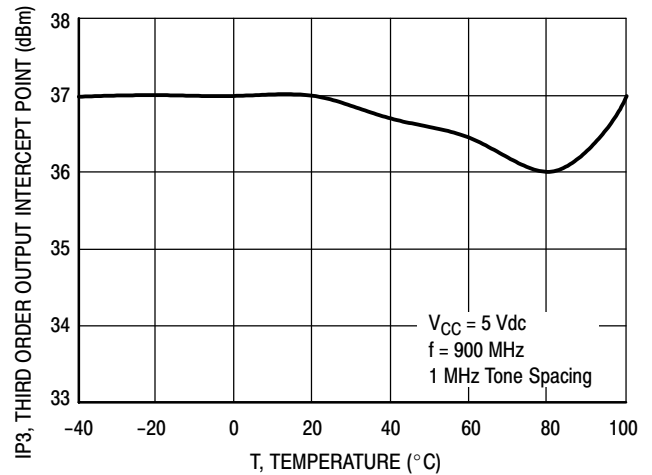


Figure 9. Third Order Output Intercept Point versus Case Temperature

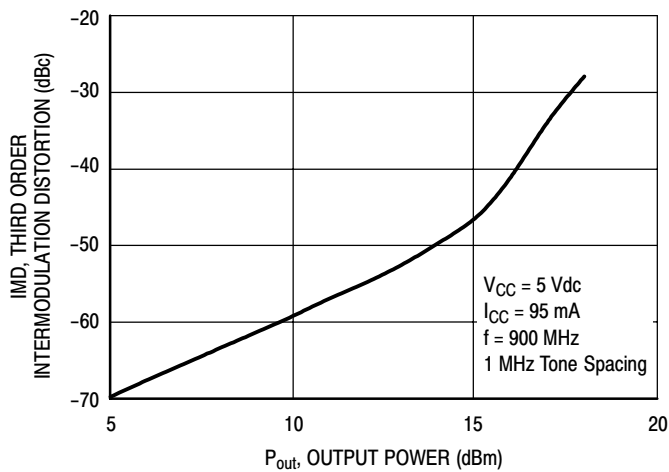
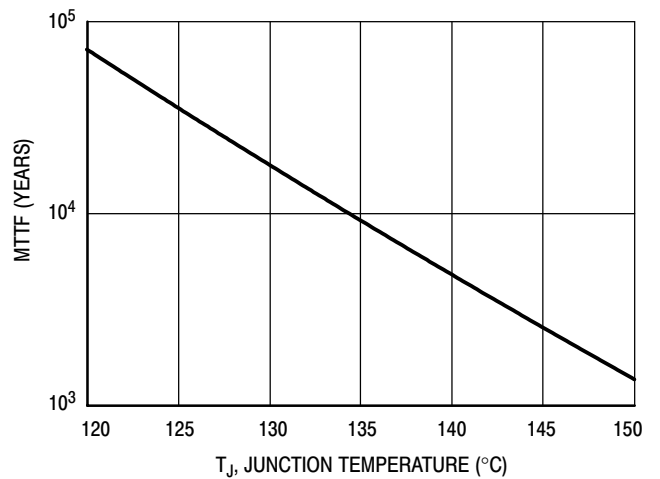


Figure 10. Third Order Intermodulation versus Output Power



NOTE: The MTTF is calculated with $V_{CC} = 5 \text{ Vdc}$, $I_{CC} = 95 \text{ mA}$

Figure 11. MTTF versus Junction Temperature

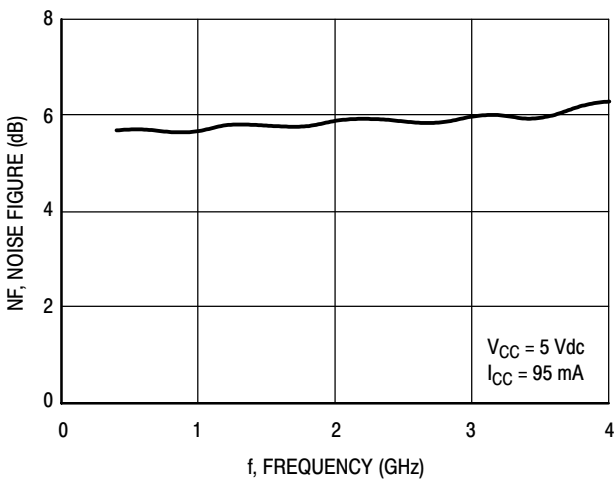


Figure 12. Noise Figure versus Frequency

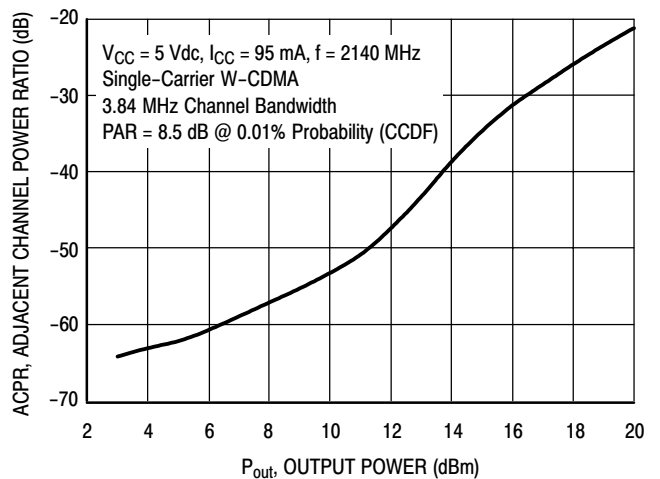


Figure 13. Single-Carrier W-CDMA Adjacent Channel Power Ratio versus Output Power

50 OHM APPLICATION CIRCUIT: 40-800 MHz

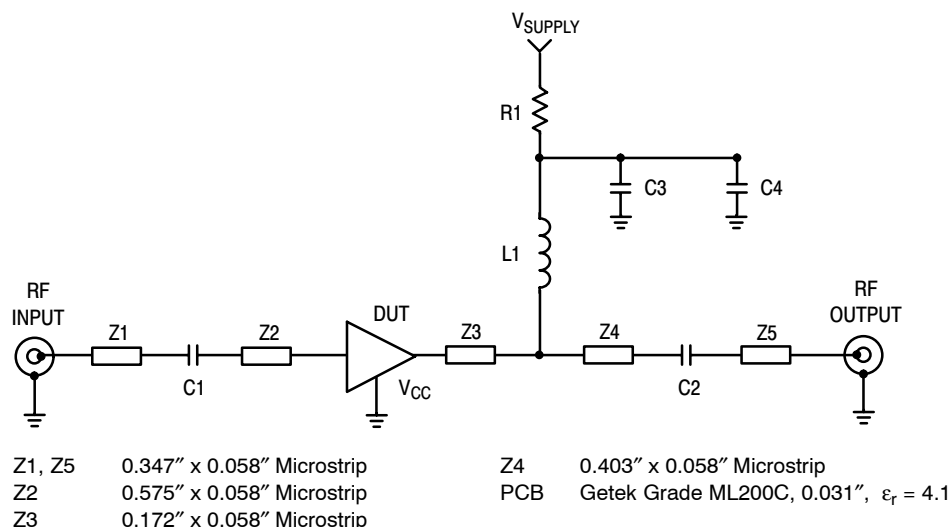


Figure 14. 50 Ohm Test Circuit Schematic

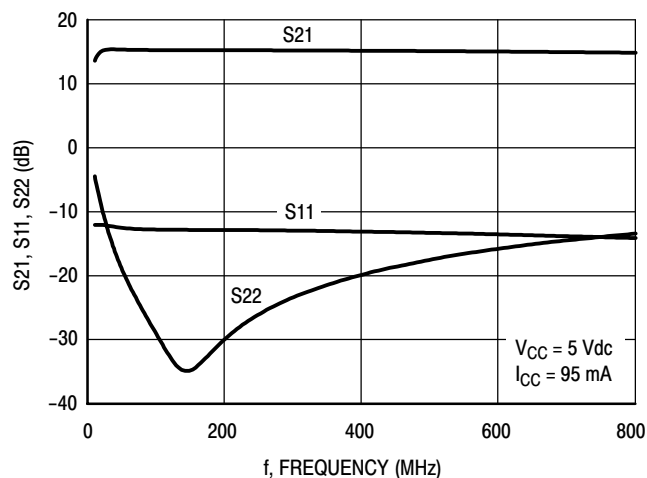


Figure 15. S21, S11 and S22 versus Frequency

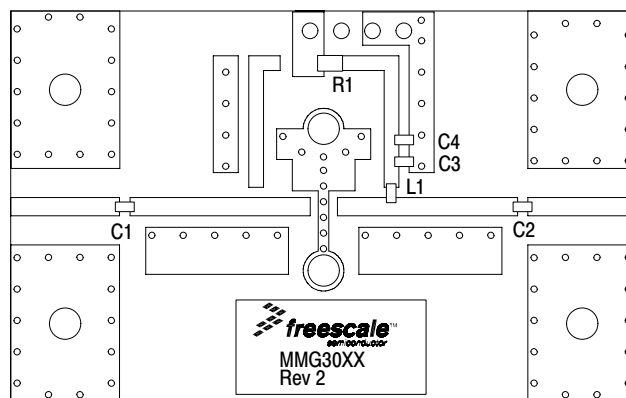


Figure 16. 50 Ohm Test Circuit Component Layout

Table 8. 50 Ohm Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1, C2	0.01 μ F Chip Capacitors	C0603C103J5RAC	Kemet
C3	0.1 μ F Chip Capacitor	C0603C104J5RAC	Kemet
C4	1 μ F Chip Capacitor	C0603C105J5RAC	Kemet
L1	470 nH Chip Inductor	BK2125HM471 - T	Taiyo Yuden
R1	0 Ω , 1/10 W Chip Resistor	CRCW06030000ZKEA	Vishay

50 OHM APPLICATION CIRCUIT: 800-3600 MHz

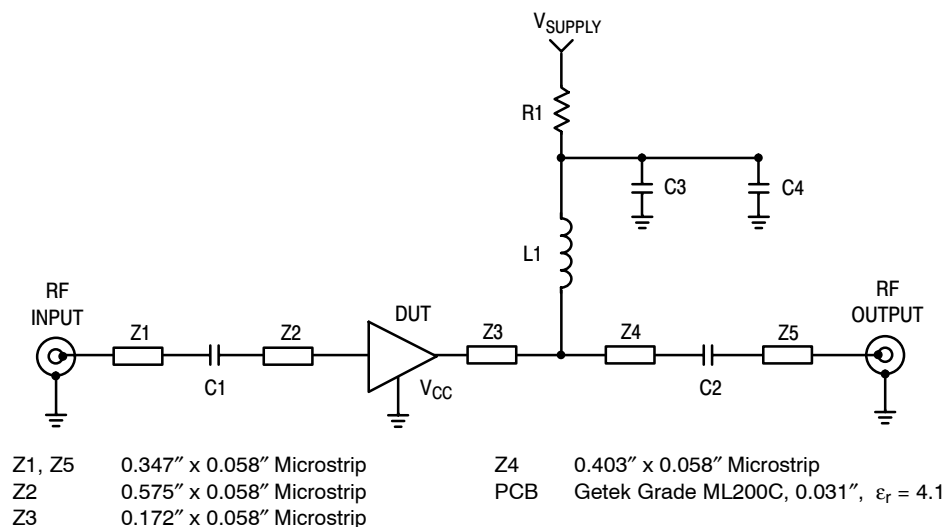


Figure 17. 50 Ohm Test Circuit Schematic

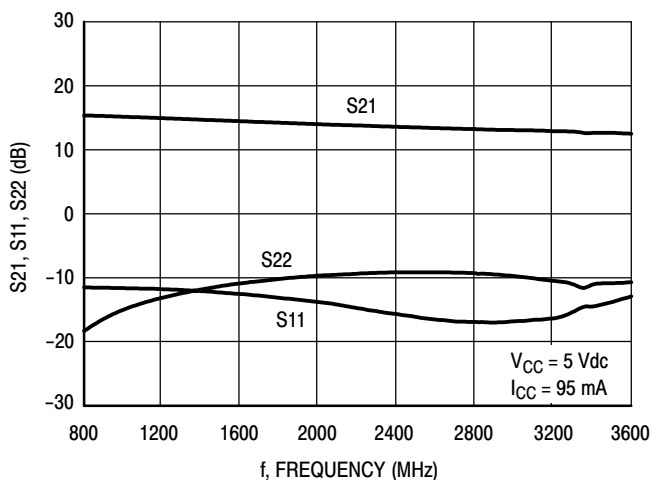


Figure 18. S21, S11 and S22 versus Frequency

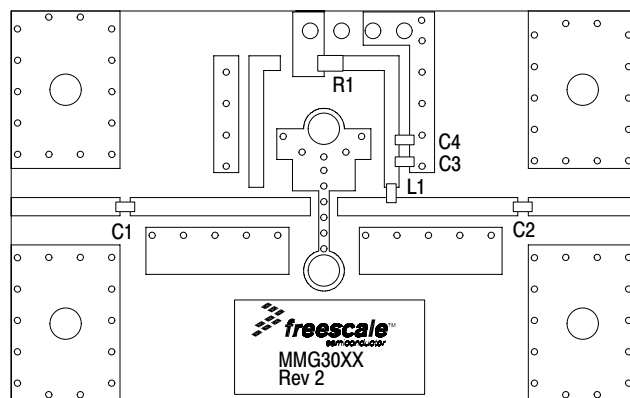


Figure 19. 50 Ohm Test Circuit Component Layout

Table 9. 50 Ohm Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1, C2	150 pF Chip Capacitors	C0603C151J5RAC	Kemet
C3	0.1 μ F Chip Capacitor	C0603C104J5RAC	Kemet
C4	1 μ F Chip Capacitor	C0603C105J5RAC	Kemet
L1	56 nH Chip Inductor	HK160856NJ-T	Taiyo Yuden
R1	0 Ω , 1/10 W Chip Resistor	CRCW06030000ZKEA	Vishay

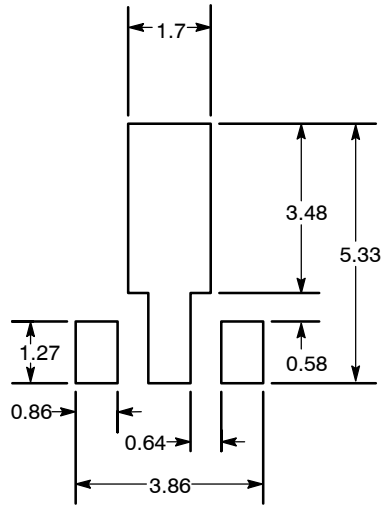
50 OHM TYPICAL CHARACTERISTICS

Table 10. Common Emitter S-Parameters ($V_{CC} = 5 \text{ Vdc}$, $I_{CC} = 95 \text{ mA}$, $T_C = 25^\circ\text{C}$, 50 Ohm System)

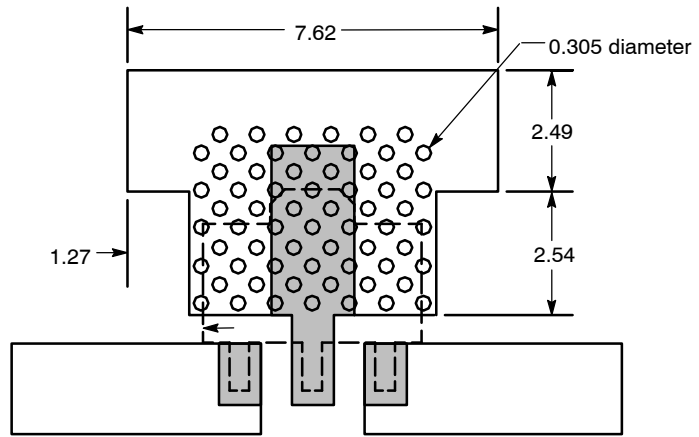
f MHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
200	0.28	174.23	6.17	171.48	0.08	-2.66	0.06	-43.26
250	0.28	172.92	6.16	169.36	0.08	-3.32	0.07	-50.81
300	0.27	171.92	6.15	167.25	0.08	-3.93	0.08	-56.75
350	0.27	170.57	6.14	165.15	0.08	-4.60	0.09	-62.45
400	0.27	169.49	6.12	163.07	0.08	-5.22	0.09	-67.13
450	0.26	168.53	6.11	160.97	0.08	-5.85	0.10	-71.09
500	0.26	167.16	6.10	158.87	0.08	-6.50	0.11	-74.88
550	0.26	165.92	6.08	156.78	0.08	-7.14	0.12	-77.99
600	0.26	164.77	6.06	154.73	0.08	-7.76	0.13	-81.75
650	0.26	163.38	6.05	152.65	0.08	-8.41	0.14	-85.06
700	0.25	162.57	6.03	150.58	0.08	-9.03	0.14	-88.16
750	0.25	161.36	6.01	148.53	0.08	-9.64	0.15	-91.28
800	0.25	160.35	5.99	146.50	0.08	-10.26	0.16	-93.96
850	0.25	159.29	5.97	144.45	0.08	-10.88	0.17	-96.90
900	0.25	158.03	5.95	142.41	0.08	-11.52	0.18	-99.99
950	0.24	157.14	5.93	140.38	0.08	-12.14	0.18	-102.70
1000	0.24	156.02	5.91	138.38	0.08	-12.78	0.19	-105.47
1050	0.24	154.89	5.88	136.37	0.08	-13.38	0.20	-108.27
1150	0.24	153.09	5.83	132.34	0.08	-14.64	0.21	-114.23
1200	0.24	152.30	5.80	130.37	0.08	-15.28	0.22	-117.17
1250	0.24	151.41	5.77	128.39	0.08	-15.94	0.22	-120.26
1300	0.24	150.63	5.75	126.41	0.08	-16.57	0.23	-123.42
1350	0.24	150.09	5.72	124.46	0.08	-17.17	0.24	-126.34
1400	0.24	149.52	5.69	122.50	0.08	-17.81	0.24	-129.61
1450	0.24	149.15	5.67	120.54	0.08	-18.46	0.25	-132.32
1500	0.23	148.71	5.65	118.61	0.08	-19.07	0.26	-134.63
1550	0.23	147.76	5.62	116.65	0.08	-19.73	0.26	-136.77
1600	0.23	146.51	5.60	114.72	0.08	-20.39	0.27	-138.90
1650	0.23	145.11	5.57	112.79	0.08	-21.04	0.28	-141.13
1900	0.23	138.41	5.41	103.23	0.08	-24.38	0.31	-152.46
2150	0.24	132.77	5.23	93.77	0.08	-27.79	0.35	-163.83
2400	0.25	128.41	5.05	84.48	0.08	-31.33	0.38	-175.54
2650	0.26	124.16	4.87	75.21	0.08	-35.09	0.40	172.45
2900	0.28	119.27	4.69	66.04	0.08	-39.03	0.43	161.50
2950	0.28	118.39	4.65	64.24	0.08	-39.86	0.44	159.35
3000	0.28	117.49	4.62	62.43	0.09	-40.65	0.44	157.23
3050	0.28	116.75	4.59	60.59	0.09	-41.48	0.45	154.83
3100	0.29	116.03	4.55	58.77	0.09	-42.33	0.46	152.37
3150	0.29	115.21	4.52	56.97	0.09	-43.16	0.46	150.02
3200	0.29	114.41	4.48	55.15	0.09	-44.01	0.47	147.68
3250	0.29	113.69	4.44	53.36	0.09	-44.83	0.48	145.58
3300	0.29	112.97	4.41	51.59	0.09	-45.67	0.48	143.48
3350	0.29	112.24	4.37	49.84	0.09	-46.48	0.49	141.43

Table 10. Common Emitter S-Parameters ($V_{CC} = 5 \text{ Vdc}$, $I_{CC} = 90 \text{ mA}$, $T_C = 25^\circ\text{C}$, 50 Ohm System) (continued)

f MHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
3400	0.29	111.50	4.34	48.07	0.09	-47.31	0.49	139.46
3450	0.29	110.37	4.30	45.96	0.09	-48.32	0.50	137.08
3500	0.29	109.50	4.27	44.53	0.09	-49.01	0.50	135.57
3550	0.29	108.57	4.23	42.83	0.09	-49.82	0.51	133.81
3600	0.29	107.57	4.20	41.14	0.09	-50.64	0.52	132.08



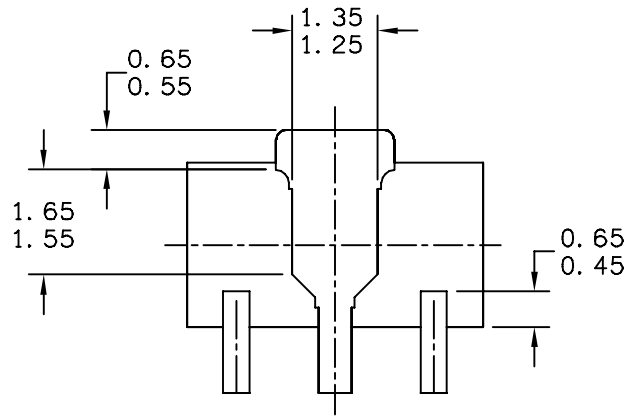
Recommended Solder Stencil



NOTES:

1. THERMAL AND RF GROUNDING CONSIDERATIONS SHOULD BE USED IN PCB LAYOUT DESIGN.
2. DEPENDING ON PCB DESIGN RULES, AS MANY VIAS AS POSSIBLE SHOULD BE PLACED ON THE LANDING PATTERN.
3. IF VIAS CANNOT BE PLACED ON THE LANDING PATTERN, THEN AS MANY VIAS AS POSSIBLE SHOULD BE PLACED AS CLOSE TO THE LANDING PATTERN AS POSSIBLE FOR OPTIMAL THERMAL AND RF PERFORMANCE.
4. RECOMMENDED VIA PATTERN SHOWN HAS 0.381 x 0.762 MM PITCH.

Figure 20. Recommended Mounting Configuration



BOTTOM VIEW

CASE STYLE:

STYLE 1:

PIN 1. RF INPUT
 PIN 2. GROUND
 PIN 3. RF OUTPUT

STYLE 2:

PIN 1. GATE
 PIN 2. SOURCE
 PIN 3. DRAIN

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TITLE: SOT-89, 4 LEAD, 4.5 X 2.5 PKG, 1.5 MM PITCH	DOCUMENT NO: 98ASA10586D	REV: D	
	CASE NUMBER: 1514-02	27 JUN 2007	
	STANDARD: NON-JEDEC		

NOTES:

1 DIMENSIONING AND TOLERANCING PER ASME Y14.5M – 1994.

2 ALL DIMENSIONS ARE IN MILLIMETERS.

3 DIMENSIONS DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.5mm PER END. DIMENSION DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.5 mm PER SIDE.

4 DIMENSION ARE DETERMINED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.

5 TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

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	CASE NUMBER: 1514-02	27 JUN 2007	
	STANDARD: NON-JEDEC		

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers
- AN3100: General Purpose Amplifier Biasing

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Aug. 2007	<ul style="list-style-type: none">• Initial Release of Data Sheet

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